L Number	Hits	Search Text	DB	Time stamp
-	16	(("6222240") or ("6020024") or ("6204203") or ("6165802") or ("6171934") or ("6115281") or ("6130103") or ("6203613")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/28 09:37
-	2932	(gate near electrode) same (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:14
-	62	((gate near electrode) same (metal near oxide)) and (hafnium or HfO or HfO2 or "HfO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:15
-	0	(MOSFET) and (gate near electrode) and (ARC near film) and (metal near oxide) and (HCl or HF or (hydrogen near chloride) or (hydrogen near fluoride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:46
-	11415	(MOSFET and (metal near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:46
-	0	((MOSFET and (metal near oxide))) and (ARC near film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:46
-	4036	((MOSFET and (metal near oxide))) and (gate near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:47
-	476	(((MOSFET and (metal near oxide))) and (gate near electrode)) and (HCl or HF or (hydrogen near chloride) or (hydrogen near fluoride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:47
-	77	((((MOSFET and (metal near oxide))) and (gate near electrode)) and (HCl or HF or (hydrogen near chloride) or (hydrogen near fluoride))) and RF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 10:50
-	621	(remove or removing or removed or removes) near (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 11:03
-	0	((remove or removing or removed or removes) near (metal near oxide)) and (without near RF)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 11:04
-	9	((remove or removing or removed or removes) near (metal near oxide)) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 11:04

-	25	(("3895966") or ("4977440") or ("5098623") or ("5173835") or ("5187636") or ("5464683") or ("5504041") or ("5528068") or ("5621681") or ("5736267") or ("5773325") or ("5786078") or ("5834353") or ("5851896") or ("5874766") or ("5876788") or ("5880006") or ("5880508") or ("5922478") or ("5923056") or ("5980977") or ("6013553") or ("6020243") or ("6096590") or ("6183846")).PN.	USPAT	2002/09/23 13:18
-	2929	((438/216) or (438/261) or (438/287) or (438/421) or (438/591) or (438/595) or (438/954) or (438/981) or (257/410) or (257/411)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:20
-	158	(((438/216) or (438/261) or (438/287) or (438/421) or (438/591) or (438/595) or (438/954) or (438/981) or (257/410) or (257/411)).CCLS.) and ((metal near oxide) same (gate near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:22
-	8	(gate near oxide) same ((vapor or vapour) near (etch or etched or etching or etches))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:26
-	1052	(438/706).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:27
-	3	((438/706).CCLS.) and (HCl and HF) and (metal near oxide) and (silicon near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:29
-	2	((438/706).CCLS.) and ((metal near oxide) with (halide or halogen or HCl or (hydrogen near chloride) or chloride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:42
-	12	(((438/712) or (438/715)).CCLS.) and (refractory near metal) same oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:23
-	503	((438/712) or (438/715)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:52
-	52	(method near (plasma near etching)) and (gate near electrode) and (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:33
-	227	(metal near oxide) same (plasma near etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:37
-	14	(metal near oxide) same (plasma near etched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:37
-	115	(metal near oxide) with (plasma near etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:38

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-	5	(metal near oxide) with (plasma near etched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:38
-	41	(hafnium near oxide) with (remove or etch or removed or etched or removing or etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 09:59
-	0	ARC near (silicon with nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:03
-	328	ARC with (silicon with nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:03
-	215	(ARC with (silicon with nitride)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:03
-	46	((ARC with (silicon with nitride)) and plasma) and (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:23
-	819	(hard near mask) with ((silicon near nitride) or SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:33
-	25	(hard near mask) with ((silicon near nitride) or SiN) with (gate near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 12:34
-	2196	((216/67) or (216/76)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 16:15
-	225	(((216/67) or (216/76)).CCLS.) and (rf and dc)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 16:15
-	20	((((216/67) or (216/76)).CCLS.) and (rf and dc)) and (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 16:21
-	86	((vapor or vapour) near phase) with (etching or etched or etch) and (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/24 16:23
-	291	(plasma near (etching or etched or etch or etches)) same (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/28 09:38